

### 1.0 SCOPE

This specification covers the detail requirements for a dual low-noise low-offset instrumentation operational amplifier.

It is highly recommended that this data sheet be used as a baseline for new military or aerospace spec control drawings.

### 1.2 Part Number. The complete part numbers per Table I of this specification follow:

<u>Device</u>	<u>Part Number</u>	<u>Package</u>
A	OP-227AY/883	Y

### 1.2.3 Case Outline.

<u>Letter</u>	<u>Case Outline (Lead finish per MIL-M-38510)</u>
Y	14-lead ceramic dual-in-line package (CERDIP)

### 1.3 Absolute Maximum Ratings. ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

Supply Voltage.....	$\pm 22\text{V}$
Internal Power Dissipation.....	500mW
Input Voltage (Note 1).....	$\pm 22\text{V}$
Differential Input Voltage (Note 2).....	$\pm 0.7\text{V}$
Differential Input Current (Note 2).....	$\pm 25\text{mA}$
Output Short-Circuit Duration.....	Indefinite
Operating Temperature Range.....	$-55^\circ\text{C}$ to $+125^\circ\text{C}$
Storage Temperature Range.....	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
Lead Temperature (Soldering, 60 sec).....	$+300^\circ\text{C}$

**NOTES:**

- For supply voltages less than  $\pm 22\text{V}$ , the absolute maximum input voltage is equal to the supply voltages.
- The OP-227 inputs are protected by back-to-back diodes. Current limiting resistors are not used in order to achieve low noise. If differential input voltage exceeds  $\pm 0.7\text{V}$ , the input current should be limited to 25mA.

### 1.5 Thermal Characteristics:

Thermal Resistance, CERDIP (Y) package:

Junction-to-Case ( $\theta_{JC}$ ) =  $29^\circ\text{C/W MAX}$

Junction-to-Ambient ( $\theta_{JA}$ ) =  $91^\circ\text{C/W MAX}$

# OP-227

**TABLE 1**

$V_S = \pm 15V$ ;  $R_S = 50\Omega$ ;  $T_A = 25^\circ C$  unless otherwise specified.

Individual Amplifier Characteristics	Symbol	Special Conditions	OP-227/883		Units
			LIMITS A		
			Min	Max	
Input Offset Voltage	$V_{OS}$		–	80	$\mu V$
		$-55^\circ C \leq T_A \leq +125^\circ C$	–	180	$\mu V$
Input Offset Current	$I_{OS}$		–	35	nA
		$-55^\circ C \leq T_A \leq +125^\circ C$	–	50	nA
Input Bias Current	$I_B$		–	$\pm 40$	nA
		$-55^\circ C \leq T_A \leq +125^\circ C$	–	$\pm 60$	nA
Input Noise Voltage (Note 1)	$e_n$	$f_O = 1\text{Hz to } 100\text{Hz}$	–	50	$nV_{RMS}$
Input Noise Current (Note 1)	$i_n$	$f_O = 1\text{Hz to } 100\text{Hz}$	–	40	$pA_{RMS}$
Input Voltage Range (Note 2)	IVR		$\pm 11$	–	V
		$-55^\circ C \leq T_A \leq +125^\circ C$	$\pm 10$	–	V
Common-Mode Rejection	CMR	$V_{CM} = IVR = \pm 11V$	114	–	dB
		$V_{CM} = IVR = \pm 10V$	108	–	dB
		$-55^\circ C \leq T_A \leq +125^\circ C$			
Power Supply Rejection Ratio	PSRR	$V_S = \pm 4V \text{ to } \pm 18V$	–	10	$\mu V/V$
		$V_S = \pm 4.5V \text{ to } \pm 18V$ $-55^\circ C \leq T_A \leq +125^\circ C$	–	16	$\mu V/V$
Large-Signal Voltage Gain	$A_{VO}$	$V_O = \pm 10V, R_L \geq 2k\Omega$	1000	–	V/mV
		$V_O = \pm 10V, R_L \geq 600\Omega$	800	–	V/mV
		$V_O = \pm 10V, R_L \geq 2k\Omega$	600	–	V/mV
		$-55^\circ C \leq T_A \leq +125^\circ C$			

**TABLE 1 (Continued)**

$V_S = \pm 15V$ ;  $R_S = 50\Omega$ ;  $T_A = 25^\circ C$  unless otherwise specified.

Individual Amplifier Characteristics	Symbol	Special Conditions	OP-227/883		Units
			LIMITS A		
			Min	Max	
Output Voltage Swing	$V_O$	$R_L \geq 2k\Omega$	$\pm 12$	—	V
		$R_L \geq 600\Omega$	$\pm 10$	—	V
		$R_L \geq 2k\Omega$	$\pm 11.5$	—	V
		$-55^\circ C \leq T_A \leq +125^\circ C$			
Power Dissipation (Each Amplifier) (Note 3)	$P_d$	$V_O = 0V$	—	140	mW
Power Supply Current (Each Amplifier)	$I_{SY}$	$V_O = 0V$	—	4.67	mA
Offset Adjustment Range	$V_{OSadj}$	$R_p = 10k\Omega$	$\pm 0.5$	—	mV
Output Short-Circuit Current	$I_{SC}^+$		—	70	mA
	$I_{SC}^-$		-70	—	mA

NOTES:

1. This test is 100% tested.
2. IVR is defined as the  $V_{CM}$  range used for the CMR test.
3.  $P_d$  is derived from  $I_{SY}$  by the relationship  $P_d = V_S * I_{SY}$ .

**TABLE 1 (Continued)**

$V_S = \pm 15V$ ;  $R_S = 50\Omega$ ;  $T_A = 25^\circ C$  unless otherwise specified.

Matching Characteristics	Symbol	Special Conditions	OP-227/883		Units
			LIMITS A		
			Min	Max	
Input Offset	$\Delta V_{OS}$		--	80	$\mu V$
Voltage Match		$-55^\circ C \leq T_A \leq +125^\circ C$	--	180	$\mu V$
Average Non-Inverting Bias Current	$I_{B^+}$	$I_{B^+} = \frac{(I_{B^+A}) + (I_{B^+B})}{2}$	--	$\pm 40$	nA
		$I_{B^+} = \frac{(I_{B^+A}) + (I_{B^+B})}{2}$	--	$\pm 60$	nA
		$-55^\circ C \leq T_A \leq +125^\circ C$			
Noninverting Offset Current	$I_{OS^+}$	$I_{OS^+} = (I_{B^+A}) - (I_{B^+B})$	--	$\pm 60$	nA
		$I_{OS^+} = (I_{B^+A}) - (I_{B^+B})$	--	$\pm 90$	nA
		$-55^\circ C \leq T_A \leq +125^\circ C$			
Inverting Offset Current	$I_{OS^-}$	$I_{OS^-} = (I_{B^-A}) - (I_{B^-B})$	--	$\pm 60$	nA
		$I_{OS^-} = (I_{B^-A}) - (I_{B^-B})$	--	$\pm 90$	nA
		$-55^\circ C \leq T_A \leq +125^\circ C$			
Common-Mode Rejection Match	$\Delta CMR$	$V_{CM} = \pm 11V$	110	--	dB
		$V_{CM} = \pm 10V$	105	--	dB
		$-55^\circ C \leq T_A \leq +125^\circ C$			
Power Supply Rejection Ratio Match	$\Delta PSRR$	$V_S = \pm 4V$ to $\pm 18V$	--	10	$\mu V/V$
		$V_S = \pm 4.5V$ to $\pm 18V$	--	16	$\mu V/V$
		$-55^\circ C \leq T_A \leq +125^\circ C$			

**TABLE 2**

OP-227/883

**Electrical Test Requirements  
For Class B Devices**

MIL-STD-883 Test Requirements	Subgroups (see Table 3)
Interim Electrical Parameters (pre Burn-In)	1
Final Electrical Test Parameters	1*, 2, 3, 4, 5, 6
Group A Test Requirements	1, 2, 3, 4, 5, 6

\* PDA applies to Subgroup 1 only.  
 $V_{OS}$  is excluded from PDA calculation.  
 No other Subgroups are included in PDA.

**TABLE 3**

**Group A Inspection**

$V_S = \pm 15V$ ;  $R_S = 50\Omega$ ;  $T_A = T_J$  unless otherwise specified.

Subgroup	Symbol	Special Conditions	OP-227/883 LIMITS A		Units
			Min	Max	
Subgroup 1 $T_A = +25^\circ C$	$V_{OS}$		--	80	$\mu V$
	$I_{OS}$		--	35	nA
	$I_B$		--	$\pm 40$	nA
	$I_{SY}$	$V_O = 0V$	--	4.67	mA
	CMR	$V_{CM} = +11V$	114	--	dB
	PSRR	$V_S = \pm 4V, \pm 18V$	--	10	$\mu V/V$
	$V_{OSadj}$		$\pm 0.5$	--	mV
	$I_{SC}^+$		--	70	mA
	$I_{SC}^-$		-70	--	mA
	$\Delta V_{OS}$		--	80	$\mu V$
	$I_B^+$	$I_B^+ = \frac{(I_{B^+A}) + (I_{B^+B})}{2}$	--	$\pm 40$	nA
	$I_{OS}^+$	$I_{OS}^+ = (I_{B^+A}) - (I_{B^+B})$	--	$\pm 60$	nA
	$I_{OS}^-$	$I_{OS}^- = (I_{B^-A}) - (I_{B^-B})$	--	$\pm 60$	nA
	$\Delta CMR$	$V_{CM} = \pm 11V$	110	--	dB
	$\Delta PSRR$	$V_S = \pm 4V, \pm 18V$	--	10	$\mu V/V$
Subgroup 2 $T_A = +125^\circ C$	$V_{OS}$		--	180	$\mu V$
	$I_{OS}$		--	50	nA
	$I_B$		--	$\pm 60$	nA

**TABLE 3**

**Group A Inspection**

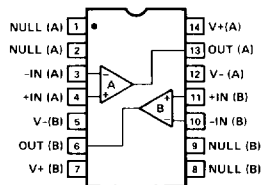
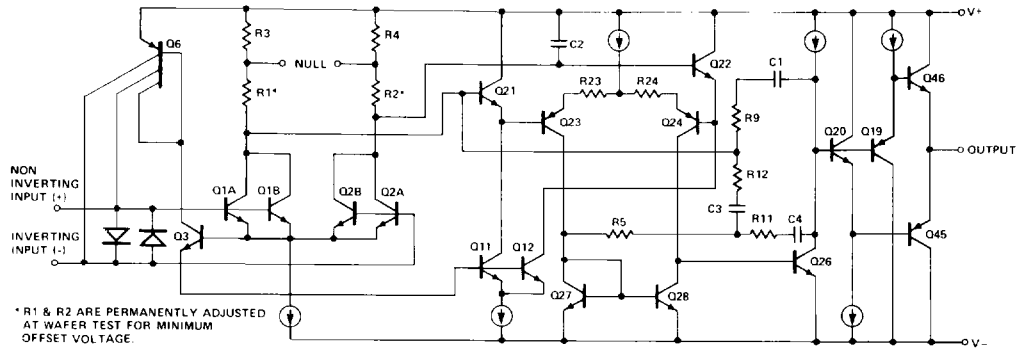
$V_S = \pm 15V$ ;  $R_S = 50\Omega$ ;  $T_A = T_J$  unless otherwise specified.

Subgroup	Symbol	Special Conditions	OP-227/883		Units
			LIMITS A		
			Min	Max	
<b>Subgroup 2</b>	CMR	$V_{CM} = \pm 10V$	108	--	dB
$T_A = +125^\circ C$	PSRR	$V_S = \pm 4.5V, \pm 18V$	--	16	$\mu V/V$
(Continued)	$\Delta V_{OS}$		--	180	$\mu V$
	$I_{B^+}$	$I_{B^+} = \frac{(I_{B^+A}) + (I_{B^+B})}{2}$	--	$\pm 60$	nA
	$I_{OS^+}$	$I_{OS^+} = (I_{B^+A}) - (I_{B^+B})$	--	$\pm 90$	nA
	$I_{OS^-}$	$I_{OS^-} = (I_{B^-A}) - (I_{B^-B})$	--	$\pm 90$	nA
	$\Delta CMR$	$V_{CM} = \pm 10V$	105	--	dB
	$\Delta PSRR$	$V_S = \pm 4.5V, \pm 18V$	--	16	$\mu V/V$
<b>Subgroup 3</b> $T_A = -55^\circ C$	All Tests, Limits and Conditions are the same as for Subgroup 2.				
<b>Subgroup 4</b>	$V_O$	$R_L = 2k\Omega$	$\pm 12$	--	V
$T_A = +25^\circ C$		$R_L = 600\Omega$	$\pm 10$	--	V
	$A_{VO}$	$V_O = \pm 10V, R_L = 2k\Omega$	1000	--	V/mV
		$V_O = \pm 10V, R_L = 600\Omega$	800	--	V/mV
<b>Subgroup 5</b>	$V_O$	$R_L = 2k\Omega$	$\pm 11.5$	--	V
$T_A = +125^\circ C$	$A_{VO}$	$V_O = \pm 10V, R_L = 2k\Omega$	600	--	V/mV
<b>Subgroup 6</b> $T_A = -55^\circ C$	All Tests, Limits and Conditions are the same as for Subgroup 5.				

# OP-227

## 3.2.1 Simplified Schematic and Pin Connections.

(1/2 OP-227)



**14-PIN CERAMIC DIP**  
(Y-Suffix)

- NOTES:**
1. Device may be operated even if insertion is reversed: this is due to inherent symmetry of pin locations of amplifiers A and B.
  2. Y- (A) and V- (B) are internally connected via substrate resistance.

**3.2.4 Microcircuit Group Assignment.** This microcircuit is covered by microcircuit group 49.

## 4.2 Life Test/Burn-In Circuit.

